

Deng-Sung Lin

List of Publications by Year in descending order

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82
papers

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citations

304743

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82
all docs

82
docs citations

82
times ranked

1450
citing authors

#	ARTICLE	IF	CITATIONS
1	Superconducting proximity effect in Ni nanoislands on $\text{Pb}(111)$. <i>Physical Review Materials</i> , 2022, 6, .		
2	Proximity-Effect-Induced Anisotropic Superconductivity in a Monolayer Ni-Pb Binary Alloy. <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 23990-23997.	8.0	3
3	Quantum well electronic states in spatially decoupled 2D Pb nanoislands on Nb-doped $\text{SrTiO}_3(001)$. <i>Applied Surface Science</i> , 2021, 537, 147967.	6.1	1
4	How dissociated fragments of multiatomic molecules saturate all active surface sites H_2 adsorption on the $\text{Si}(100)$ surface. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 404004.	1.8	4
5	Imaging buried objects with the hard/soft x-ray photoemission electron microscope. <i>Journal of Applied Physics</i> , 2021, 130, 175307.	2.5	2
6	Extended Γ -phase Bi atomic layer on $\text{Si}(111)$ fabricated by thermal desorption. <i>Applied Surface Science</i> , 2020, 504, 144103.	6.1	6
7	Orbital-enhanced warping effect in px,py-derived Rashba spin splitting of monatomic bismuth surface alloy. <i>Npj Quantum Materials</i> , 2020, 5, .	5.2	7
8	Controlling the Polarity of the Molecular Beam Epitaxy Grown In-Bi Atomic Film on the $\text{Si}(111)$ Surface. <i>Scientific Reports</i> , 2019, 9, 756.	3.3	6
9	Atomic-Scale Chemical Conversion of Single-Layer Transition Metal Dichalcogenides. <i>ACS Nano</i> , 2019, 13, 5611-5615.	14.6	2
10	Depth Dependence of the Photoelectron Emission Profile for Cathode Lens Microscopy. <i>Microscopy and Microanalysis</i> , 2018, 24, 156-157.	0.4	3
11	Growth of a predicted two-dimensional topological insulator based on InBi-Si(111)- $\sqrt{7} \times \sqrt{7}$ surface reconstruction. <i>Physical Review B</i> , 2018, 98, .		
12	Large quantum-spin-Hall gap in single-layer $1T' \text{WSe}_2$. <i>Nature Communications</i> , 2018, 9, 2003.	12.8	117
13	Growth of Ge and Si on Monolayer Silicene on Metal Surfaces. , 2018, , 155-161.		1
14	Tunable electronic structure and surface states in rare-earth monobismuthides with partially filled d shell. <i>Physical Review B</i> , 2018, 98, .	3.2	31
15	Ordered 2D Structure Formed upon the Molecular Beam Epitaxy Growth of Ge on the Silicene/Ag(111) Surface. <i>ACS Omega</i> , 2016, 1, 357-362.	3.5	6
16	Few-Layer Silicon Films on the Ag(111) Surface. <i>Journal of Physical Chemistry C</i> , 2016, 120, 2698-2702.	3.1	13
17	Separation of the attractive and repulsive contributions to the adsorbate-adsorbate interactions of polar adsorbates on $\text{Si}(100)$. <i>Surface Science</i> , 2015, 641, 282-288.	1.9	7
18	Bonding and interface formation for Si on Ag(111) by core-level photoemission spectroscopy. <i>Applied Surface Science</i> , 2015, 354, 212-215.	6.1	6

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19	Gold atomic clusters extracting the valence electrons to shield the carbon monoxide passivation on near-monolayer core-shell nanocatalysts in methanol oxidation reactions. <i>Physical Chemistry Chemical Physics</i> , 2015, 17, 15131-15139.	2.8	10
20	Growth mode and structures of silicene on the Ag(111) surface. <i>Applied Surface Science</i> , 2015, 354, 187-195.	6.1	12
21	Heterojunction confinement on the atomic structure evolution of near monolayer core-shell nanocatalysts in redox reactions of a direct methanol fuel cell. <i>Journal of Materials Chemistry A</i> , 2015, 3, 1518-1529.	10.3	34
22	Atomic and Electronic Processes during the Formation of an Ionic NaCl Monolayer on a Covalent Si(100) Surface. <i>Journal of Physical Chemistry C</i> , 2012, 116, 11526-11538.	3.1	7
23	Iodine Adsorption on Arrays, Clusters, and Pairs of Reactive Sites on the Si(100) Surface. <i>Journal of Physical Chemistry C</i> , 2012, 116, 3091-3096.	3.1	8
24	Energetics and Interactions of Mixed Halogen Adsorbates on the Si(100) Surface. <i>Journal of Physical Chemistry C</i> , 2011, 115, 13268-13274.	3.1	8
25	Adsorption of Diatomic Interhalogens on the Si(100) and Ge(100) Surfaces. <i>Journal of Physical Chemistry C</i> , 2011, 115, 13262-13267.	3.1	6
26	Adsorption and abstraction reactions of HCl on a single Si(100) dangling bond. <i>Physical Review B</i> , 2011, 83, .	3.2	10
27	Sodium chloride on Si(100) grown by molecular beam epitaxy. <i>Physical Review B</i> , 2011, 83, .	3.2	8
28	Determination of dissociative fragment-adsorbate interaction energy during chemisorption of the diatomic molecule HCl on Si(100). <i>Physical Review B</i> , 2010, 81, .	3.2	9
29	Formation, Binding, and Stability of O-Ag-CO ₂ -Ag-O Compounds on Ag(100) Investigated by Low Temperature Scanning Tunneling Microscopy and Manipulation. <i>Journal of Physical Chemistry C</i> , 2010, 114, 14173-14179.	3.1	6
30	Mediation of chain reactions by propagating radicals during halogenation of H-masked Si(100): Implications for atomic-scale lithography and processing. <i>Journal of Chemical Physics</i> , 2009, 130, 164706.	3.0	11
31	Electronic reconstruction at a buried ionic-covalent interface driven by surface reactions. <i>Physical Review B</i> , 2009, 80, .	3.2	3
32	Possibility of direct exchange diffusion of hydrogen on the Si-Cl surface. <i>Physical Review B</i> , 2009, 80, .	3.2	8
33	Hard repulsive barrier in hot adatom motion during dissociative adsorption of oxygen on Ag(100). <i>Journal of Chemical Physics</i> , 2009, 131, 174709.	3.0	17
34	Growth mode and novel structure of ultra-thin KCl layers on the Si(100)-2 \times 1 surface. <i>Surface Science</i> , 2009, 603, 419-424.	1.9	7
35	Atomic and electronic structures of thin NaCl films grown on a Ge(001) surface. <i>Surface Science</i> , 2009, 603, 2102-2107.	1.9	8
36	Ion Segregation and Deliquescence of Alkali Halide Nanocrystals on SiO ₂ . <i>Journal of Physical Chemistry A</i> , 2009, 113, 9715-9720.	2.5	12

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37	Correlation of reaction sites during the chlorine extraction by hydrogen atom from Cl-terminated Si(100)-1x1. Journal of Chemical Physics, 2007, 127, 034708.	3.0	2
38	Apparent Topographic Height Variations Measured by Noncontact Atomic Force Microscopy. Japanese Journal of Applied Physics, 2007, 46, 4395-4402.	1.5	7
39	Evolution of Two-Dimensional Structure Phase Transitions (3x1) and (1x1) on Hydrogen-Terminated Si(100) Surface. Japanese Journal of Applied Physics, 2006, 45, 2197-2199.	1.5	0
40	Growth behaviour of Ge nano-islands on the nanosized Si{111} facets bordering on two {100} planes. Nanotechnology, 2006, 17, 5207-5211.	2.6	2
41	Lin and Chiang Reply. Physical Review Letters, 2006, 96, .	7.8	1
42	Systematic variations in apparent topographic height as measured by noncontact atomic force microscopy. Physical Review B, 2006, 74, .	3.2	2
43	Atomistic View of the Recombinative Desorption of H ₂ from H/Si(100). Physical Review Letters, 2005, 94, 196103.	7.8	12
44	Stability and mechanism of selective etching of ultrathin Ge films on the Si(100) surface upon chlorine adsorption. Physical Review B, 2004, 69, .	3.2	3
45	Atomistics of Ge Deposition on Si(100) by Atomic Layer Epitaxy. Physical Review Letters, 2003, 90, 046102.	7.8	39
46	Thermal reactions on the Cl-terminated SiGe(100) surface. Surface Science, 2002, 507-510, 295-299.	1.9	5
47	Comparison of thermal reactions of phosphine on Ge(1 0 0) and Si(1 0 0) by high-resolution core-level photoemission. Surface Science, 2001, 482-485, 654-658.	1.9	18
48	Structure study of GaN:Mg films by X-ray absorption near-edge structure spectroscopy. Solid State Communications, 2001, 117, 577-582.	1.9	2
49	Chlorine-induced Si surface segregation on the Ge-terminated Si/Ge(100) surface from core-level photoemission. Physical Review B, 2001, 64, .	3.2	10
50	Gallium K-edge x-ray absorption study on Mg-doped GaN. Applied Physics Letters, 2001, 78, 31-33.	3.3	8
51	Gallium K-edge EXAFS study of GaN:Mg films. , 2000, 4078, 535.		0
52	Interaction of phosphine with Si(100) from core-level photoemission and real-time scanning tunneling microscopy. Physical Review B, 2000, 61, 2799-2805.	3.2	31
53	Distribution of dangling bond pairs on partially hydrogen-terminated Si(100) surface observed by scanning tunneling microscopy. Surface Science, 2000, 454-456, 196-200.	1.9	3
54	Hydrogen-desorption kinetic measurement on the Si(100)-2x1:H surface by directly counting desorption sites. Physical Review B, 1999, 60, R8461-R8464.	3.2	26

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55	Influence of Sapphire Nitridation on Properties of Indium Nitride Prepared by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1999, 38, 645-648.	1.5	22
56	Thermal reactions of phosphine with Si(100): a combined photoemission and scanning-tunneling-microscopy study. Surface Science, 1999, 424, 7-18.	1.9	65
57	Real-time scanning tunneling microscopy observation of Si(100) $\sqrt{2 \times 1}$ to $\sqrt{2 \times n}$ to $\sqrt{4 \times 4}$ structural phase transitions. Surface Science, 1998, 397, L273-L279.	1.9	13
58	Scanning tunneling microscopy observation of surface reconstruction of Si(100) during chemical vapor deposition from Si ₂ H ₆ . Surface Science, 1998, 402-404, 831-835.	1.9	9
59	Growth mode in Si(100) $\sqrt{2 \times 1}$ epitaxy by low-temperature chemical-vapor deposition. Physical Review B, 1998, 57, 12421-12427.	3.2	16
60	Atomic-level investigation of the growth of Si/Ge by ultrahigh vacuum chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 919-926.	2.1	5
61	Growth process of Ge on Si(100)- $\sqrt{2 \times 1}$ in atomic-layer epitaxy from Ge ₂ H ₆ . Physical Review B, 1997, 56, 4878-4886.	3.2	28
62	Coverage-dependent thermal reactions of digermane on Si(100)- $\sqrt{2 \times 1}$. Physical Review B, 1996, 54, 16958-16964.	3.2	12
63	X-ray truncation rod study of Ge(001) surface roughening by molecular beam homoepitaxial growth. Journal of Applied Physics, 1996, 79, 6858-6864.	2.5	4
64	Boundary-structure determination of Ag/Si(111) interfaces by x-ray diffraction. Physical Review B, 1995, 52, 1839-1847.	3.2	34
65	Atomic burrowing and hole formation for Au growth on Ag(110). Surface Science, 1995, 323, L299-L304.	1.9	25
66	X-ray study of the interface. Surface Science, 1995, 339, L891-L896.	1.9	3
67	Surface segregation and growth mode transitions during the initial stages of Si growth on Ge(001) $\sqrt{2 \times 1}$ by cyclic gas-source molecular beam epitaxy from Si ₂ H ₆ . Journal of Applied Physics, 1994, 75, 240-247.	2.5	25
68	Holography of Ge(111) $\sqrt{2 \times 8}$ by Surface Core-Level Photoemission. Physical Review Letters, 1994, 73, 3117-3120.	7.8	40
69	Adsorption, thermal reaction, and desorption of disilane on Ge(111)- $\sqrt{2 \times 8}$. Physical Review B, 1994, 49, 1836-1843.	3.2	2
70	Growth and atomic structure of epitaxial Si films on Ge(111). Surface Science, 1994, 312, 213-220.	1.9	9
71	Adsorption and dissociation of Si ₂ H ₆ on Ge(001) $\sqrt{2 \times 1}$. Surface Science, 1993, 280, 265-276.	1.9	32
72	Thermal reactions of disilane on Si(100) studied by synchrotron-radiation photoemission. Physical Review B, 1993, 48, 11846-11850.	3.2	12

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73	Adsorption and thermal reactions of disilane and the growth of Si films on Ge(100)-(2 \times 1). Physical Review B, 1993, 47, 6543-6554.	3.2	34
74	Scanning-tunneling-microscopy studies of disilane adsorption and pyrolytic growth on Si(100)-(2 \times 1). Physical Review B, 1992, 45, 3494-3498.	3.2	74
75	X-ray scattering study of Ag/Si(111) buried interface structures. Physical Review Letters, 1992, 68, 507-510.	7.8	50
76	Lin et al. reply. Physical Review Letters, 1992, 69, 552-553.	7.8	13
77	Si indiffusion on Ge(100)-(2 \times 1) studied by core-level photoemission. Physical Review B, 1992, 45, 11415-11418.	3.2	27
78	C ₆₀ encapsulation of the Si(111)-(7 \times 7) surface. Applied Physics Letters, 1992, 61, 3127-3129.	3.3	29
79	Bonding of Cs on Si and Ge surfaces studied by core-level spectroscopy. Physical Review B, 1991, 44, 10719-10723.	3.2	24
80	Charge transfer and asymmetry on Ge(111)-(2 \times 8) studied by scanning tunneling microscopy. Physical Review B, 1991, 44, 1403-1406.	3.2	71
81	Dimer charge asymmetry determined by photoemission from epitaxial Ge on Si(100)-(2 \times 1). Physical Review Letters, 1991, 67, 2187-2190.	7.8	56
82	Calorimetric and optical microscopic studies on one ferroelectric liquid-crystal compound with the smectic-A phase. Physical Review A, 1989, 40, 4153-4156.	2.5	23